



Correction to: Effect of Silicon Doping on the Electrical Performance of Amorphous SiInZnO Thin-film Transistors

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Unfortunately, the original publication of the article was published without keywords. The keywords are given in this correction.

Keywords

Thin-Film transistor

Silicon doping

Low-frequency noise

X-ray photoelectron spectroscopy

The original article has been corrected.

The original article can be found online at <https://doi.org/10.1007/s42341-021-00285-5>.

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